

SPECIFICATION AMENDMENTS

Please amend paragraph 0027 as follows:

Thus, at least one additional valve (i.e., ISO valve 30) can be connected to throttle valve 28 via line 21, such that throttle valve 28 and the additional valve 30 are connected in series with each other between process chamber 20 and pump 32. One or more lines 15 [[14]], 17, and 19 (i.e., gas and/or liquid delivery line) can be connected to pump 32 and process chamber 20. One or more pressure gauges 14, 16 and 18 may be connected respectively to lines 15, 17 and 19 between pump 32 and process chamber 20.

Please amend paragraph 0028 as follows:

Pressure gauges 14, 16 and 18 may together form a grouping or plurality pressure gauges 13, which can be utilized to sense the backside 12 pressure of a wafer 24 within process chamber 20. Note that although three pressure gauges 14, 15, and 18 are illustrated in FIG. 1, the particular number of pressure gauges utilized is not considered a limiting feature of the present invention, so long as such pressure gauges are utilized to monitor a wafer backside pressure.

Please amend paragraph 0035 as follows:

FIG. 3 illustrates a block diagram 70 [[40]] of a chamber configuration for plasma etching under wafer transfer shift conditions, in accordance with a preferred embodiment of the present invention. As indicated in FIG. 3, a semiconductor wafer 84 generally placed on a lower electrode 83 in a process chamber 82 of a plasma etching device. Such process chambers can be utilized in plasma etching operations. Wafer 84 (i.e., semiconductor wafer) generally comprises a front side and a backside ~~back-side~~. A differential pressure gradient between the front side and the ~~back-side~~ of wafer 84 can thus be determined, and thereafter, a position of wafer 84 on lower electrode 83 can be measured utilizing the differential pressure gradient. Process chamber 82 is generally connected to a pump 72. Gas flow into process chamber 82 is generally represented by arrow 80.